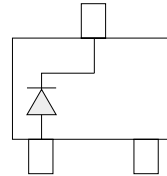


SWITCHING DIODE

FEATURES

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance

MARKING : A6



BAS16



MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V _{RM}	100	V
Peak Repetitive Peak Reverse Voltage	V _{RRM}	75	V
Working Peak Reverse Voltage	V _{RWM}		
DC Blocking Voltage	V _R		
RMS Reverse Voltage	V _{R(RMS)}	53	V
Forward Continuous Current	I _{FM}	300	mA
Average Rectified Output Current	I _O	150	mA
Peak Forward Surge Current @t=1.0μs	I _{FSM}	2.0	A
		@t=1.0s	
Power Dissipation	P _D	225	mW
Thermal Resistance Junction to Ambient	R _{θJA}	556	°C/W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{STG}	-55~+150	°C

Electrical Ratings @TA=25°C

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	V _(BR)	I _R = 100μA	75		V
Reverse voltage leakage current	I _R	V _R =75V		1	μA
Forward voltage	V _F	I _F =1mA		0.715	V
		I _F =10mA		0.855	
		I _F =50mA		1	
Diode capacitance	C _D	V _R =0, f=1MHz		2	pF
Reveres recovery time	t _{rr}	I _F =I _R =10mA, I _{rr} =0.1×I _R , R _L =100Ω		6	ns

BAS16 Typical Characteristics

